

L	Hits	Search Text	DB	Time stamp
Number		1: -:1:-id- add film	USPAT;	2002/04/24
-	1330	tungsten adj silicide adj film	US-PGPUB;	11:34
			EPO; JPO;	11.54
			DERWENT;	
			IBM TDB	
		(tungsten adj silicide adj film) and	USPAT;	2002/04/23
_	0	"PH.sub.3" and "WF.sub.4" and "SiCl.sub.2	US-PGPUB;	14:57
		"PH. Sub. 3" and Wr. Sub. 4 and Sici. Sub. 2	EPO; JPO;	11.07
		H.sub.2" and "Ar"	DERWENT;	
			IBM TDB	
		//	USPAT;	2002/04/23
-	1330	(tungsten adj silicide adj film) "WF.sub.4" and "SiCl.sub.2 H.sub.2" and	US-PGPUB;	14:57
			EPO; JPO;	14.57
		"Ar"	DERWENT;	
			IBM TDB	
		(tungsten adj silicide adj film) and	USPAT;	2002/04/23
-	0	"WF.sub.4" and "SiCl.sub.2 H.sub.2" and	US-PGPUB;	14:57
		"Ar"	EPO; JPO;	14.57
			DERWENT;	
			IBM TDB	
	60	(tungsten adj silicide adj film) and	USPAT;	2002/04/23
	69	"PH.sub.3"	US-PGPUB;	14:58
		"Ph. sub. 3"	EPO; JPO;	11.30
			DERWENT;	· ·
			IBM TDB	
	100	(tungsten adj silicide) near5 phosphorus	USPAT;	2002/04/24
	103	(tungsten ad) silicide, hears phosphoras	US-PGPUB;	11:35
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	6	(tungsten adj silicide) near5 (phosphorus near3 gas)	USPAT;	2002/04/24
			US-PGPUB;	11:36
			EPO; JPO;	ļ
			DERWENT;	
			IBM TDB	
_	736	(tungsten adj silicide) and (polysilicon	USPAT;	2002/04/24
	,30	adj layer) and silicon and (anneal or	US-PGPUB;	14:02
		annealing or annealed) and (oxidizing or	EPO; JPO;	
		oxidation or oxidize)	DERWENT;	
			IBM TDB	
_	51	((tungsten adj silicide) and (polysilicon	USPAT;	2002/04/24
		adj layer) and silicon and (anneal or	US-PGPUB;	16:06
		annealing or annealed) and (oxidizing or	EPO; JPO;	
		oxidation or oxidize)) and ((oxidation or	DERWENT;	
		oxidizing or oxidize) near5 (sidewall or	IBM_TDB	
		(side adj wall)))	_	· _